RGS80TS65HR

650V 40A Field Stop Trench IGBT

Datasheet

V _{CES}	650V
I _{C (100°C)}	40A
V _{CE(sat) (Typ.)}	1.65V
P_{D}	272W

Outline TO-247N (1)(2)(3)

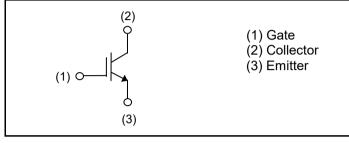
Features

- 1) Low Collector Emitter Saturation Voltage
- 2) Short Circuit Withstand Time 8µs
- 3) Qualified to AEC-Q101
- 4) Pb free Lead Plating; RoHS Compliant

Application

Heater for Automotive

●Inner Circuit



Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Tuno	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGS80TS65

● **Absolute Maximum Ratings** (at T_C = 25°C unless otherwise specified)

		1		
Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V _{GES}	±30	V
Collector Current	T _C = 25°C	I _C	73	Α
	T _C = 100°C	I _C	40	Α
Pulsed Collector Current		I _{CP} *1	120	Α
Power Dissipation	T _C = 25°C	P _D	272	W
	T _C = 100°C	P _D	136	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{imax.}

●Thermal Resistance

Parameter	Symbol	Values			Unit
raiametei	Зуппон	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	1	ı	0.55	°C/W

●IGBT Electrical Characteristics (at T_i = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Linit
			Min.	Тур.	Max.	Unit
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	-	-	V
		$V_{CE} = 650V, V_{GE} = 0V,$				
Collector Cut - off Current	I _{CES}	$T_{j} = 25^{\circ}C$ $T_{j} = 175^{\circ}C^{*2}$	-	-	10	μΑ
		Tj = 175°C ^{*2}	ı	ı	5	mA
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$V_{CE} = 5V, I_{C} = 2.0mA$	5.0	6.0	7.0	V
		$I_C = 40A, V_{GE} = 15V,$				
Collector - Emitter Saturation Voltage	$V_{\text{CE(sat)}}$	T _j = 25°C	-	1.65	2.10	V
		T _j = 175°C	-	2.15	-	V

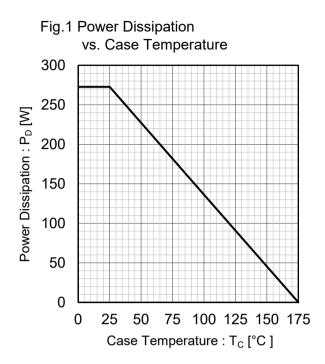
●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Dorometer	Symbol	Conditions		Limit		
Parameter			Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	V _{CE} = 30V,	-	1240	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$,	-	103	-	pF
Reverse transfer Capacitance	C_{res}	f = 1MHz	-	16	-	
Total Gate Charge	Q_g	V _{CE} = 300V,	-	48	1	
Gate - Emitter Charge	Q_{ge}	I _C = 40A,	-	12	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	19	-	
Turn - on Delay Time	t _{d(on)}		-	37	-	
Rise Time	t _r	$I_C = 40A, V_{CC} = 400V,$ $V_{GE} = 15V, R_G = 10\Omega,$	-	17	-	no
Turn - off Delay Time	$t_{d(off)}$	$T_i = 25^{\circ}C$	-	112	-	ns
Fall Time	t _f	Inductive Load	-	96	-	
Turn - on Switching Loss	E _{on}	*E _{on} include diode reverse recovery	-	1.05	-	mJ
Turn - off Switching Loss	E _{off}	,	-	1.03	-	
Turn - on Delay Time	t _{d(on)}		-	34	-	
Rise Time	t _r	$I_C = 40A, V_{CC} = 400V,$ $V_{GF} = 15V, R_G = 10\Omega,$	-	28	-	ns
Turn - off Delay Time	t _{d(off)}	$T_i = 175^{\circ}C$	-	141	-	
Fall Time	t _f	Inductive Load	-	150	-	
Turn - on Switching Loss	E _{on}	*E _{on} include diode reverse recovery	-	1.43	-	
Turn - off Switching Loss	E _{off}	10001001000019	-	1.47	-	mJ
Reverse Bias Safe Operating Area	RBSOA	$I_C = 120A$, $V_{CC} = 520V$, $V_P = 650V$, $V_{GE} = 15V$, $R_G = 50\Omega$, $T_j = 175^{\circ}C$	FULL SQUARE		-	
Short Circuit Withstand Time	t _{sc}	$V_{CC} \le 360V$, $V_{GE} = 15V$, $T_j = 25^{\circ}C$	8	-	-	μs
Short Circuit Withstand Time	t _{sc} *2	$V_{CC} \le 360V$, $V_{GE} = 15V$, $T_j = 150$ °C	6	-	-	μs

^{*2} Design assurance without measurement

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• Electrical Characteristic Curves



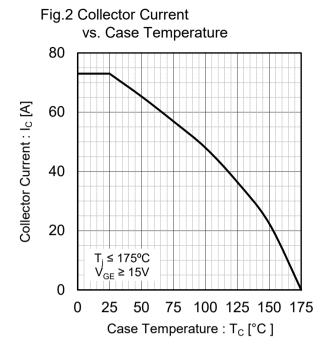


Fig.3 Forward Bias Safe Operating Area 1000 10µs 100 Collector Current : I_C [A] 10 100µs 1 0.1 $T_C = 25^{\circ}C$ Single Pulse 0.01 10 100 1000 Collector To Emitter Voltage: V_{CE} [V]

140 120 Collector Current : Ic [A] 100 80 60 40 20 $T_i \le 175^{\circ}C$ V_{GF} = 15V 0 200 400 600 800 Collector To Emitter Voltage: V_{CE} [V]

Fig.4 Reverse Bias Safe Operating Area

•Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

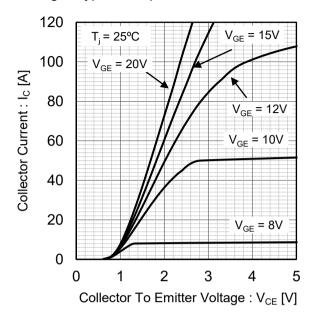


Fig.6 Typical Output Characteristics

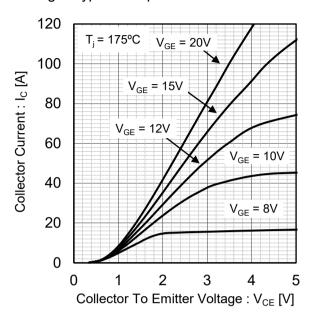


Fig.7 Typical Transfer Characteristics

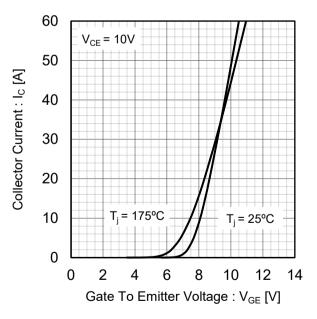
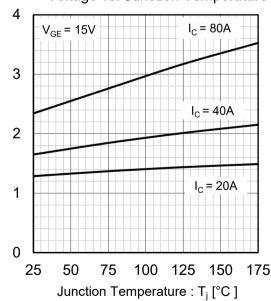


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Collector To Emitter Saturation Voltage

 $: V_{CE(sat)}[V]$

0

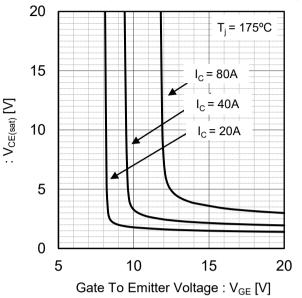
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Electrical Characteristic Curves

Voltage vs. Gate To Emitter Voltage 20 $T_{j} = 25^{\circ}\text{C}$ $T_{j} = 25^{\circ}\text{C}$ $T_{c} = 80\text{A}$ $T_{c} = 40\text{A}$ $T_{c} = 20\text{A}$ $T_{c} =$

Fig.9 Typical Collector To Emitter Saturation

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



 $\begin{array}{cc} & 10 & 15 \\ \text{Gate To Emitter Voltage : V}_{\text{GE}}\left[V\right] \end{array}$

20

Fig.11 Typical Switching Time vs. Collector Current

1000 t_i $t_{d(off)}$ 100 $t_{d(off)}$ $t_{d(off)}$

vs. Gate Resistance 1000 Switching Time [ns] 100 $t_{d(off)}$ $t_{d(on)}$ 10 V_{CC} = 400V, I_C = 40A, V_{GE} = 15V, T_j = 175°C Inductive load 1 0 10 20 30 40 50 Gate Resistance : $R_G [\Omega]$

Fig.12 Typical Switching Time

•Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current

10 E_{off} $V_{CC} = 400V, V_{GE} = 15V, R_{G} = 10\Omega, T_{J} = 175^{\circ}C$ Inductive load

0 10 20 30 40 50 60 70 80

Collector Current: I_{C} [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ] E_{on} 1 E_{off} 0.1 V_{CC} = 400V, I_{C} = 40A, V_{GE} = 15V, T_{j} = 175°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance : $R_G[\Omega]$

Fig.14 Typical Switching Energy Losses

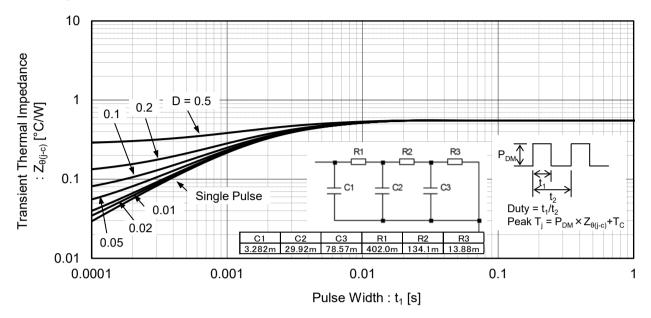
Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 C_{ies} 1000 Capacitance [pF] C_oes 100 10 $\mathsf{C}_{\mathsf{res}}$ f = 1MHz $V_{GE} = 0V$ $T_i = 25^{\circ}C$ 1 0.01 0.1 10 100 Collector To Emitter Voltage: V_{CE} [V]

15 V_{CE} = 200V Gate To Emitter Voltage: VGE [V] $V_{CE} = 300V$ 10 V_{CE} = 400V 5 $I_C = 40A$ T_i = 25°C 0 0 10 20 30 40 50 Gate Charge : Qq [nQ]

Fig.16 Typical Gate Charge

•Electrical Characteristic Curves

Fig.17 IGBT Transient Thermal Impedance



●Inductive Load Switching Circuit and Waveform

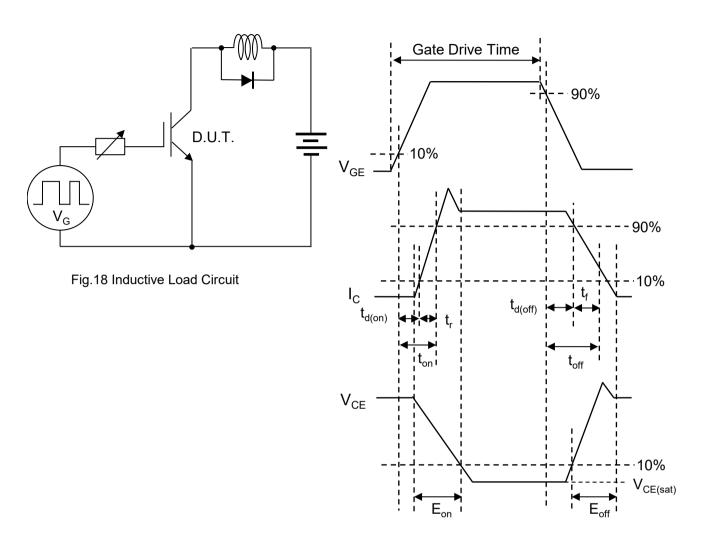


Fig.19 Inductive Load Waveform

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